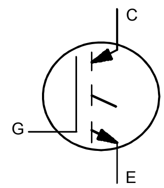
AUTOMOTIVE GRADE

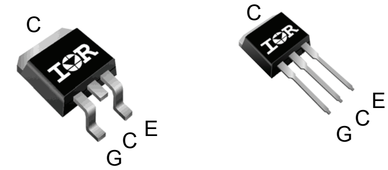
AUIRGS30B60K
AUIRGSL30B60K

INSULATED GATE BIPOLAR TRANSISTOR



n-channel

V_{CES} = 600V
I_C = 50A, T_C = 100C
At T_J = 175°C
$t_{SC} \geq$ 10µs, T_J = 150°C
$V_{CE(on)}$ typ. = 1.95V



AUIRGS30B60K
D^2Pak

AUIRGSL30B60K
TO-262Pak

G	C	E
Gate	Collector	Emitter

Features

- Low $V_{CE\ (on)}$ Non Punch Through IGBT Technology
- 10µs Short Circuit Capability
- Square RBSOA
- Positive $V_{CE\ (on)}$ Temperature Coefficient.
- Maximum Junction Temperature rated at 175°C
- Lead-Free, RoHS Compliant
- Automotive Qualified * *

Benefits

- Benchmark Efficiency for Motor Control
- Rugged Transient Performance for Increased Reliability
- Low EMI
- Excellent Current Sharing in Parallel Operation

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
AUIRGSL30B60K	TO-262	Tube	50	AUIRGSL30B60K
AUIRGS30B60K	D^2 Pak	Tube	50	AUIRGS30B60K
		Tape and Reel Left	800	AUIRGS30B60KTRL
		Tape and Reel Right	800	AUIRGS30B60KTRR

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
I_C @ T_C = 25°C	Continuous Collector Current	78	A
I_C @ T_C = 100°C	Continuous Collector Current	50	
I_{CM}	Pulse Collector Current (Ref.Fig.C.T.5)	120	
I_{LM}	Clamped Inductive Load Current ①	120	
V_{ISOL}	RMS Isolation Voltage, Terminal to Case, t=1 min.	2500	V
V_{GE}	Continuous Gate-to-Emitter Voltage	±20	
P_D @ T_C = 25°C	Maximum Power Dissipation	370	W
P_D @ T_C = 100°C	Maximum Power Dissipation	180	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +175	°C
	Soldering Temperature, for 10 sec.	300 (0.063 in.(1.6mm) from case)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance Junction-to-Case (IGBT)	——	——	0.41*	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink (flat, greased surface)	——	0.50	——	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (typical socket mount)	——	——	40	
Wt	Weight	——	1.44	——	g

* $R_{\theta JC}$ (end of life) = 0.65°C/W. This is the maximum measured value after 1000 temperature cycles from -55 to 150°C and is accounted for by the physical wearout of the die attach medium.

** Qualification standards can be found at www.infineon.com

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	Ref. Fig.
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	V_{GE} = 0V, I_C = 500µA	
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.40	—	V/°C	V_{GE} = 0V, I_C = 1mA (25°C-150°C)	
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	1.95	2.35	V	I_C = 30A, V_{GE} = 15V, T_J = 25°C	5,6,7
		—	2.40	2.75		I_C = 30A, V_{GE} = 15V, T_J = 150°C	8,9,10
		—	2.6	2.95		I_C = 30A, V_{GE} = 15V, T_J = 175°C	
$V_{GE(th)}$	Gate Threshold Voltage	3.5	4.5	5.5	V	I_C = 250µA	8,9,10,
$\Delta V_{GE(th)}/\Delta TJ$	Threshold Voltage temp. coefficient	—	-10	—	mV/°C	V_{CE} = V_{GE}, I_C = 1.0mA (25°C-150°C)	11
gfe	Forward Transconductance	—	18	—	S	V_{CE} = 50V, I_C = 50A,PW = 80µs	
I_{CES}	Collector-to-Emitter Leakage Current	—	5.0	250	µA	V_{GE} = 0V, V_{CE} = 600V	
			1000	2000		V_{GE} = 0V, V_{CE} = 600V,T_J = 150°C	
		—	1830	3000		V_{GE} = 0V, V_{CE} = 600V,T_J = 175°C	
I_{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V_{GE} = ±20V, V_{CE} = 0V	

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	Ref. Fig.
Q_g	Total Gate Charge (turn-on)	—	102	153	nC	I_C = 30A	17
Q_{ge}	Gate-to-Emitter Charge (turn-on)	—	14	21		V_{GE} = 15V	CT1
Q_{gc}	Gate-to-Collector Charge (turn-on)	—	44	66		V_{CC} = 400V	
E_{on}	Turn-On Switching Loss	—	350	620	µJ	I_C = 30A, V_{CC} = 400V,	CT4
E_{off}	Turn-Off Switching Loss	—	825	955		V_{GE} = +15V,	
E_{total}	Total Switching Loss	—	1175	1575		R_G = 10Ω, L = 200µH, T_J = 25°C ③	
$t_{d(on)}$	Turn-On delay time	—	46	60	ns		
t_r	Rise time	—	28	39			
$t_{d(off)}$	Turn-Off delay time	—	185	200			
t_f	Fall time	—	31	40			
E_{on}	Turn-On Switching Loss	—	635	1085	µJ	I_C = 30A, V_{CC} = 400V,	12,14, CT4 WF1,WF2
E_{off}	Turn-Off Switching Loss	—	1150	1350		V_{GE} = +15V,	
E_{total}	Total Switching Loss	—	1785	2435		R_G = 10Ω, L = 200µH, T_J = 150°C	
$t_{d(on)}$	Turn-On delay time	—	46	60	ns		13,15 CT4 WF1 WF2
t_r	Rise time	—	28	39			
$t_{d(off)}$	Turn-Off delay time	—	205	235			
t_f	Fall time	—	32	42			
L_E	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package	
C_{ies}	Input Capacitance	—	1750	—	pF	V_{GE} = 0V	16
C_{oes}	Output Capacitance	—	160	—		V_{CC} = 30V	
C_{res}	Reverse Transfer Capacitance	—	60	—		f = 1.0Mhz	
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				T_J = 150°C, I_C = 120A,Vp = 600V V_{CC} = 500V, V_{GE} = +15V to 0V Rg = 10Ω	4 CT2
SCSOA	Short Circuit Safe Operating Area	10	—	—	µs	T_J = 150°C, Vp = 600V ,Rg = 10Ω V_{CC} = 360V, V_{GE} = +15V to 0V	CT3 WF3
I_{SC} (Peak)	Peak Short Circuit Collector Current	—	200	—	A		WF3

Notes:

① V_{CC} = 80% (V_{CES}), V_{GE} = 20V, L = 28µH, R_G = 22Ω.
② This is applied to D2Pak, when mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.
③ Energy losses include "tail" and diode reverse recovery.

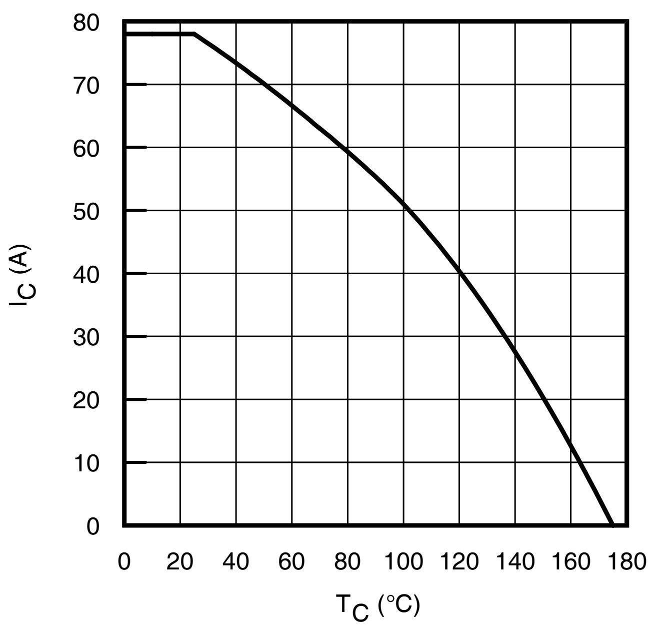


Fig. 1 - Maximum DC Collector Current vs. Case Temperature

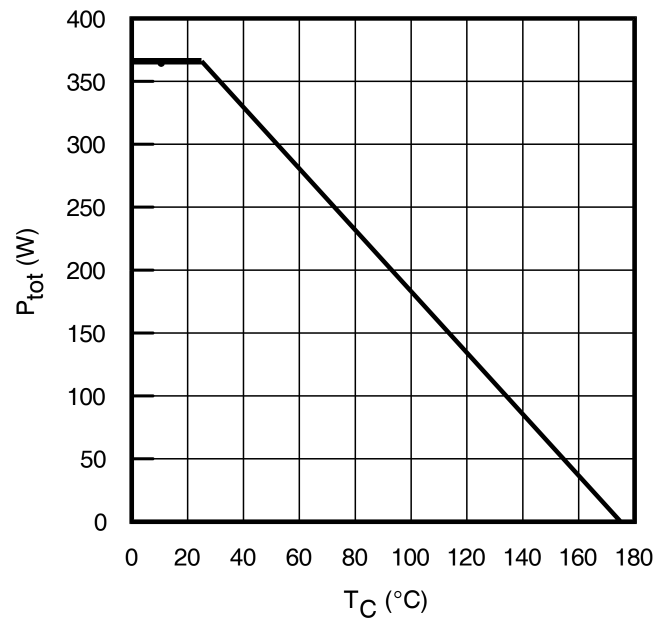


Fig. 2 - Power Dissipation vs. Case Temperature

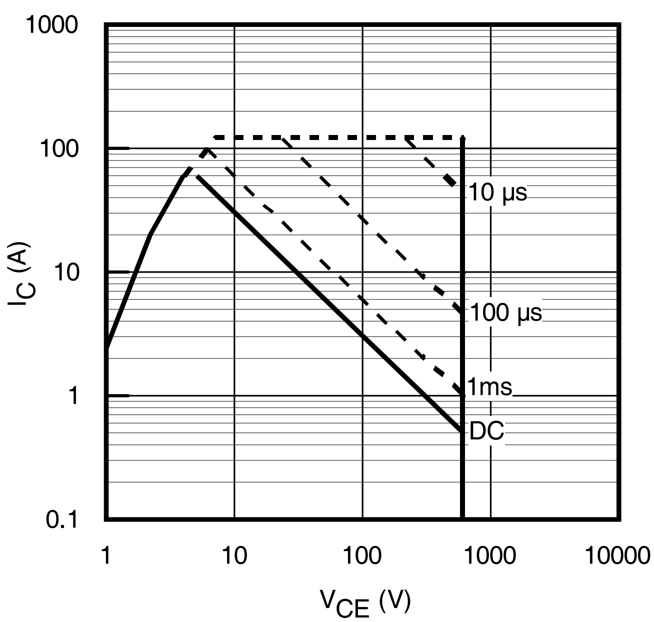


Fig. 3 - Forward SOA

T_C = 25°C, $T_J \leq$ 150°C

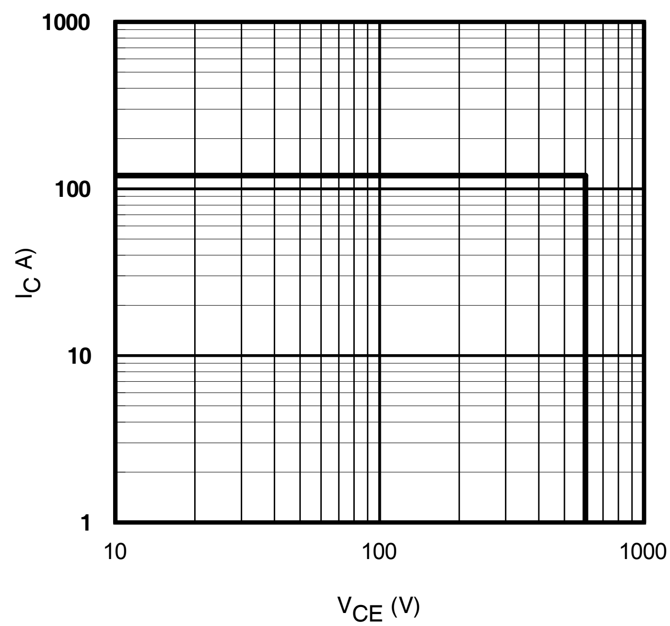


Fig. 4 - Reverse Bias SOA

T_J = 150°C; V_{GE} =15V

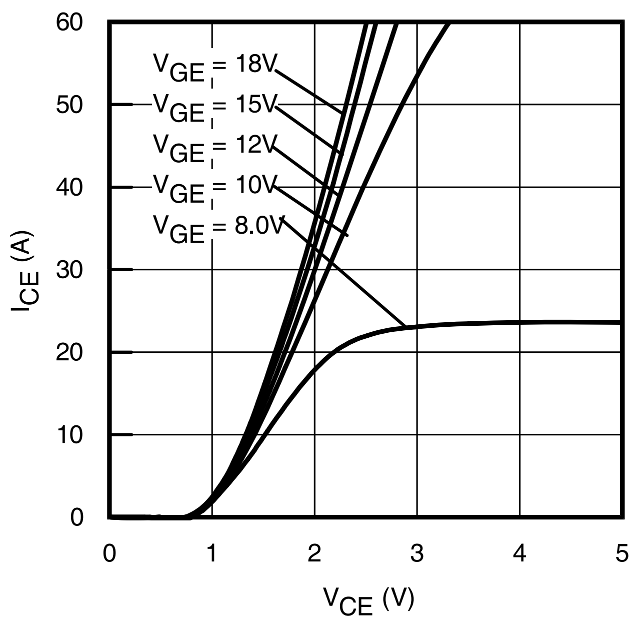


Fig. 5 - Typ. IGBT Output Characteristics
T_J = -40°C; tp = 80µs

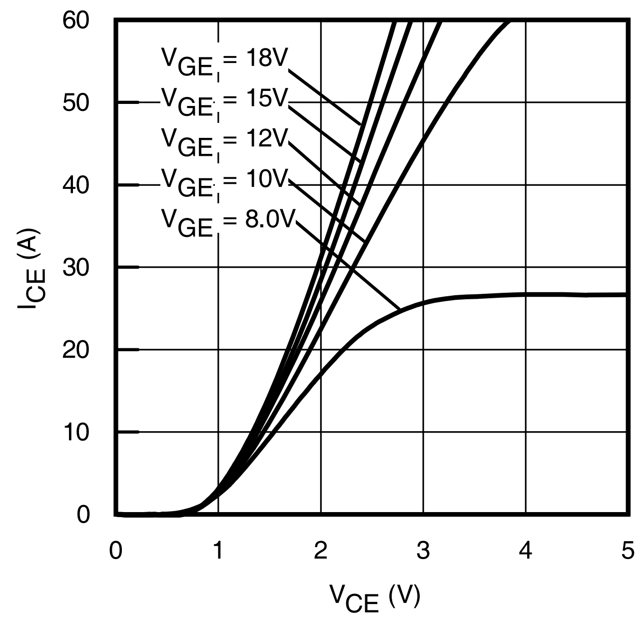


Fig. 6 - Typ. IGBT Output Characteristics
T_J = 25°C; tp = 80µs

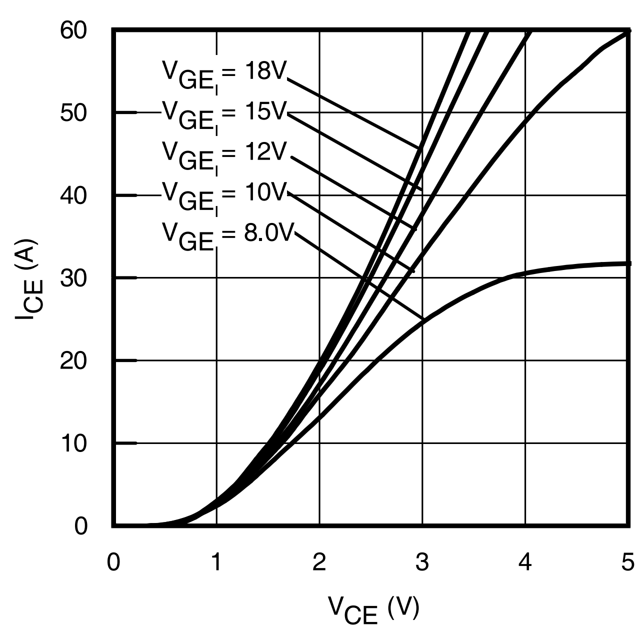


Fig. 7 - Typ. IGBT Output Characteristics
T_J = 150°C; tp = 80µs

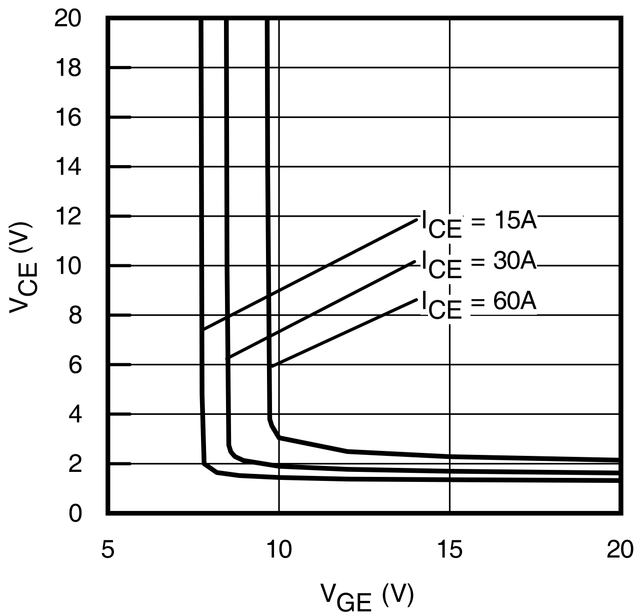


Fig. 8 - Typical V_{CE} vs. V_{GE}
T_J = -40°C

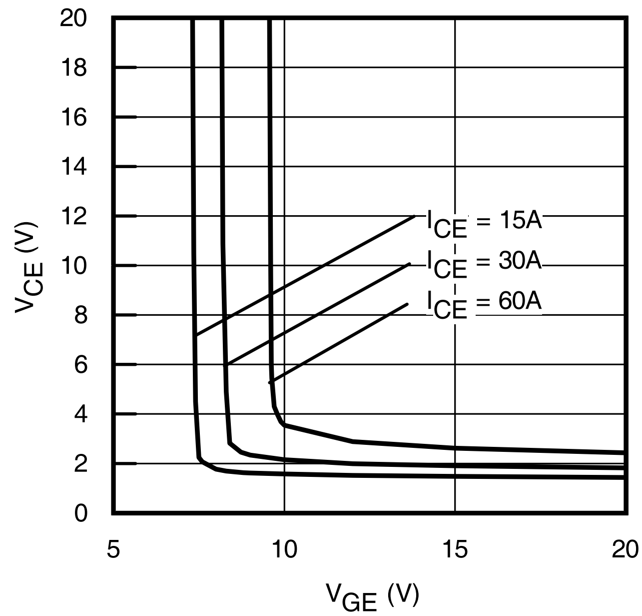


Fig. 9 - Typical V_{CE} vs. V_{GE}
T_J = 25°C

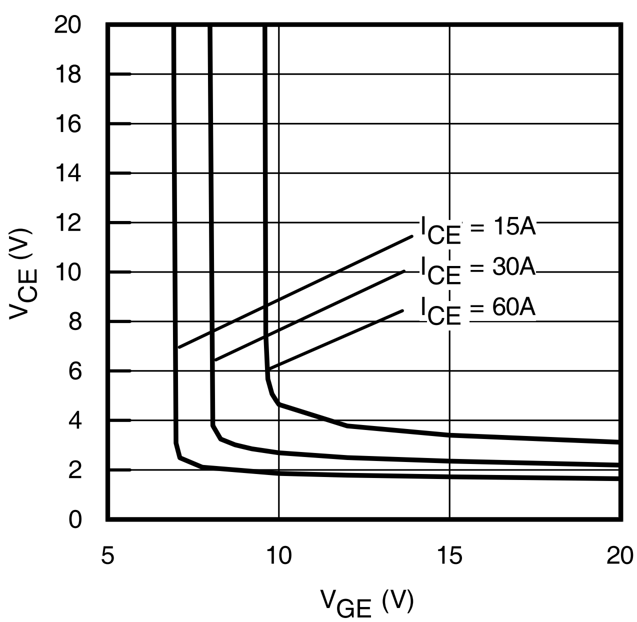


Fig. 10 - Typical V_{CE} vs. V_{GE}
T_J = 150°C

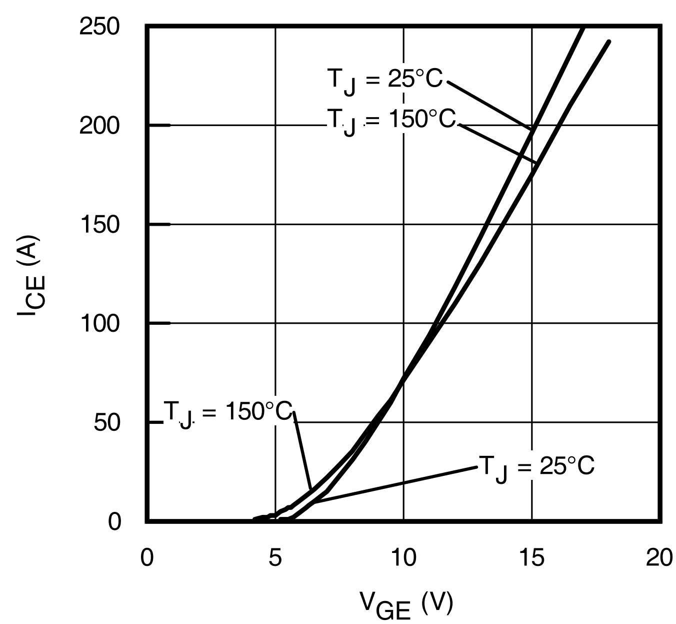


Fig. 11 - Typ. Transfer Characteristics
V_{CE} = 50V; tp = 10µs

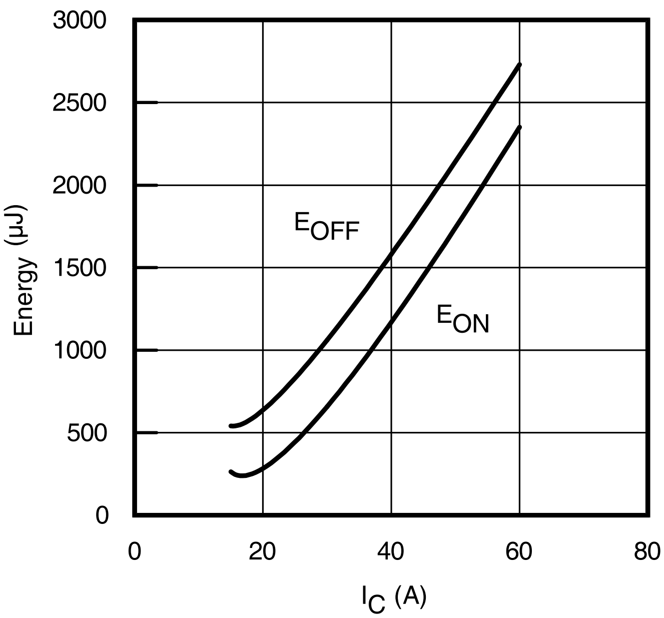


Fig. 12- Typ. Energy Loss vs. I_C
T_J = 150°C; L = 200µH; V_{CE} = 400V, R_G = 10Ω; V_{GE} = 15V

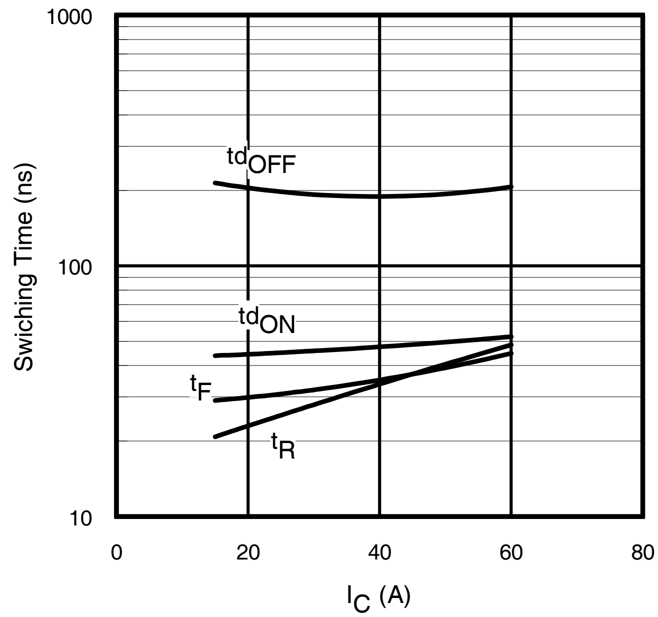


Fig. 13 - Typ. Switching Time vs. I_C
T_J = 150°C; L = 200µH; V_{CE} = 400V, R_G = 10Ω; V_{GE} = 15V

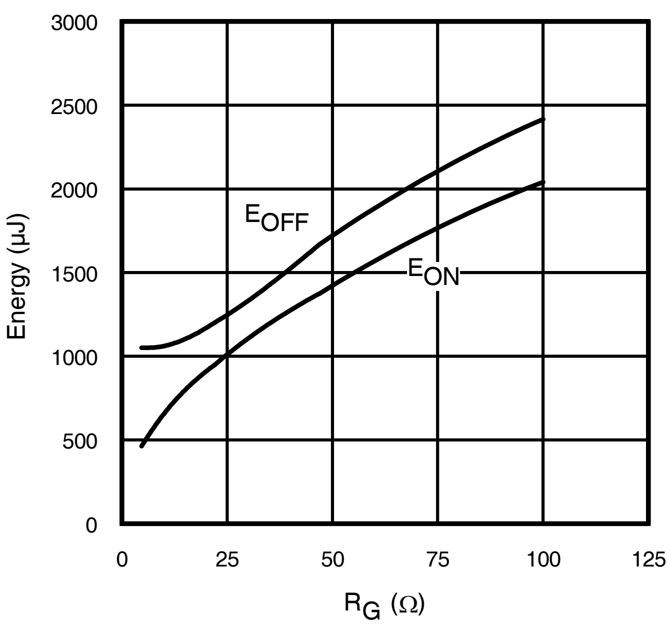


Fig. 14 - Typ. Energy Loss vs. R_G
T_J = 150°C; L = 200µH; V_{CE} = 400V, I_{CE} = 30A; V_{GE} = 15V

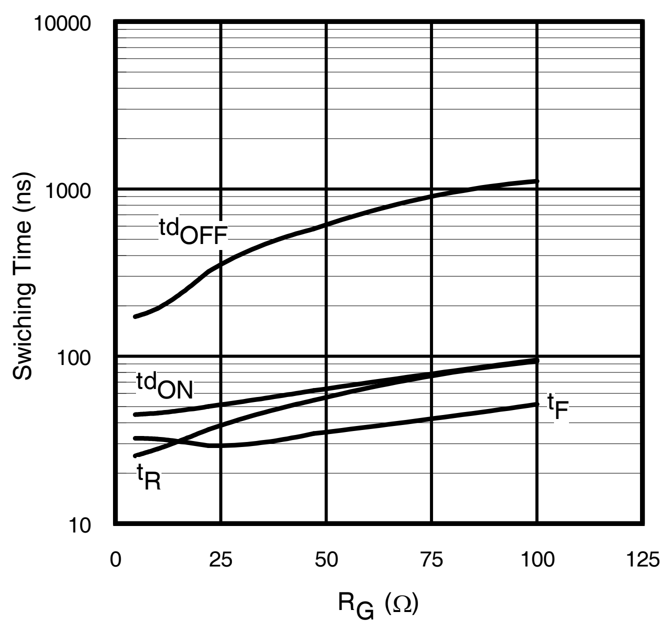


Fig. 15 - Typ. Switching Time vs. R_G
T_J = 150°C; L = 200µH; V_{CE} = 400V, I_{CE} = 30A; V_{GE} = 15V

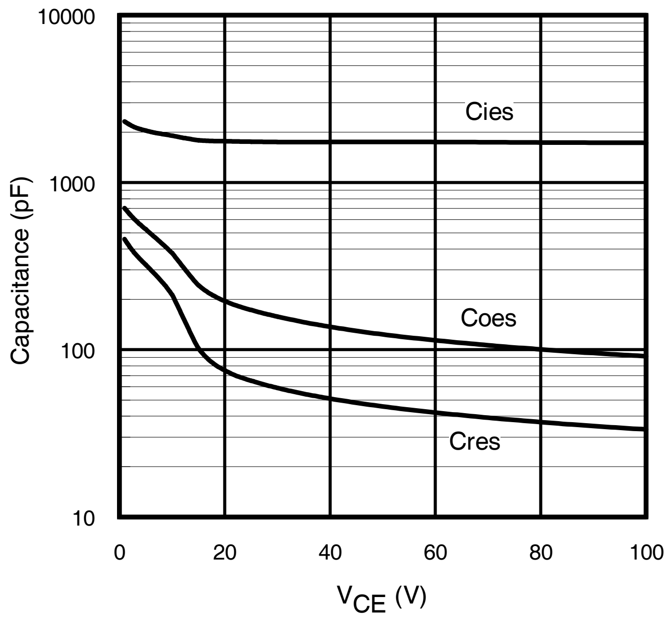


Fig. 16- Typ. Capacitance vs. V_{CE}
V_{GE}= 0V; f = 1MHz

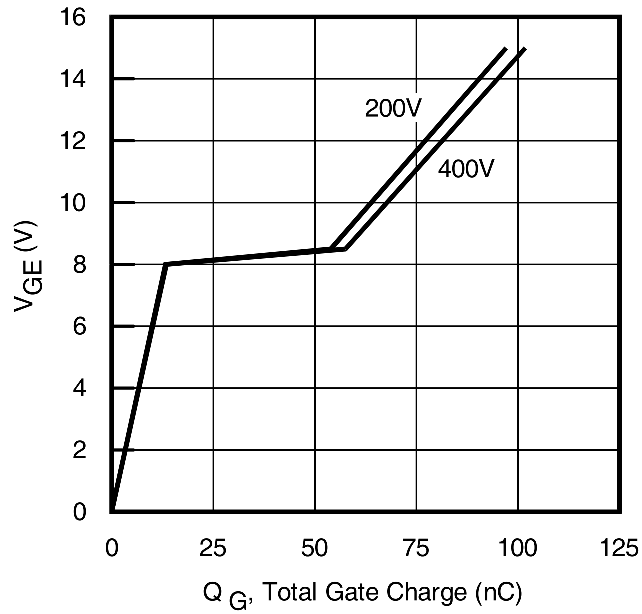
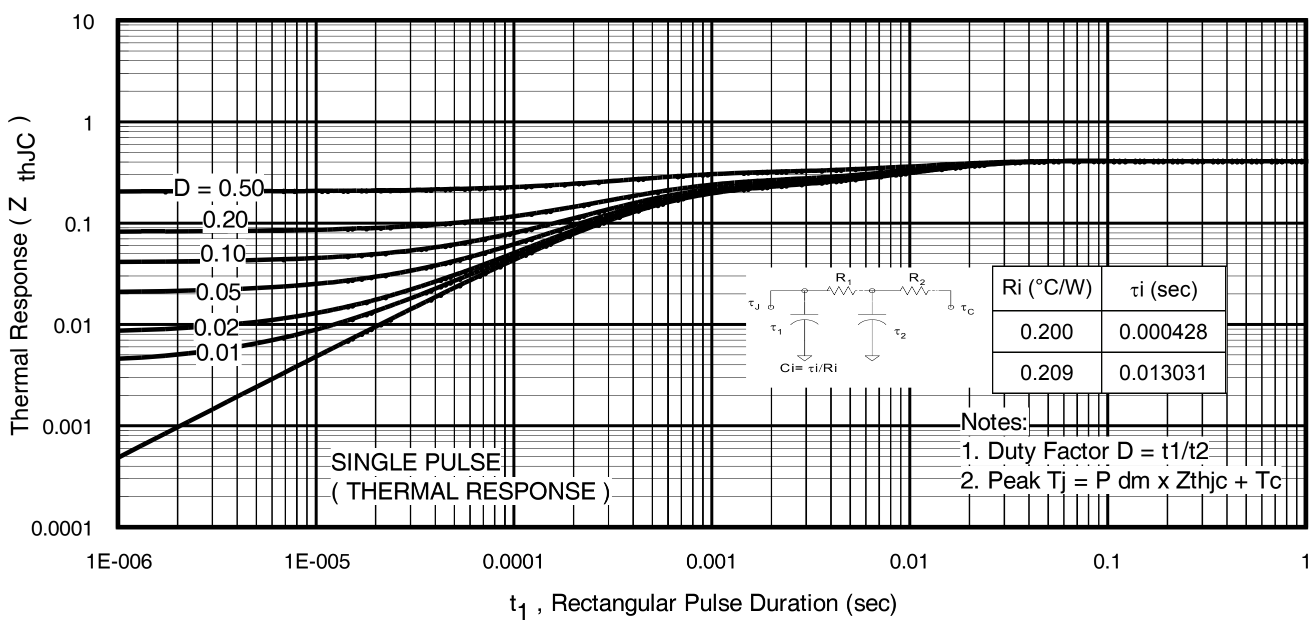


Fig. 17 - Typical Gate Charge vs. V_{GE}
I_{CE} = 30A; L = 600µH



Ri (°C/W)	τi (sec)
0.200	0.000428
0.209	0.013031

Fig 18. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)

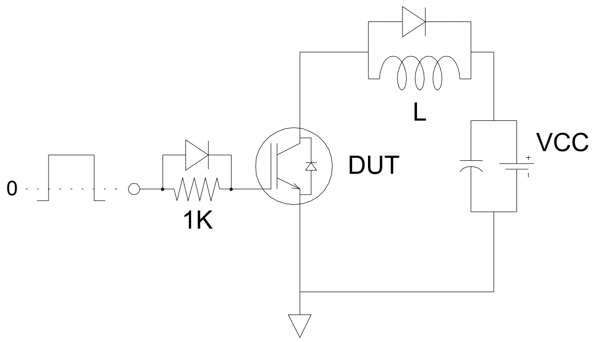


Fig.C.T.1 - Gate Charge Circuit (turn-off)

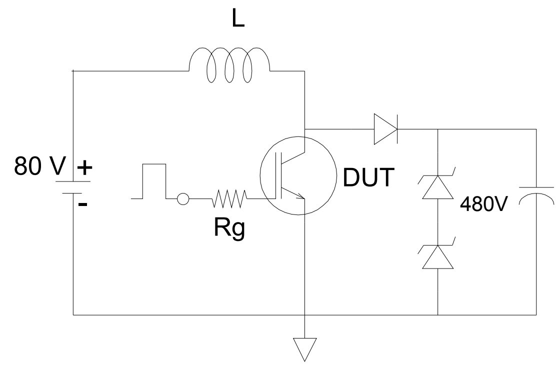


Fig.C.T.2 - RBSOA Circuit

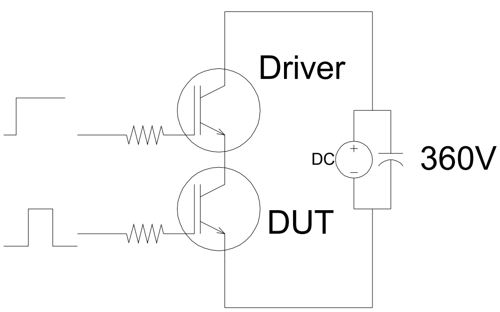


Fig.C.T.3 - S.C. SOA Circuit

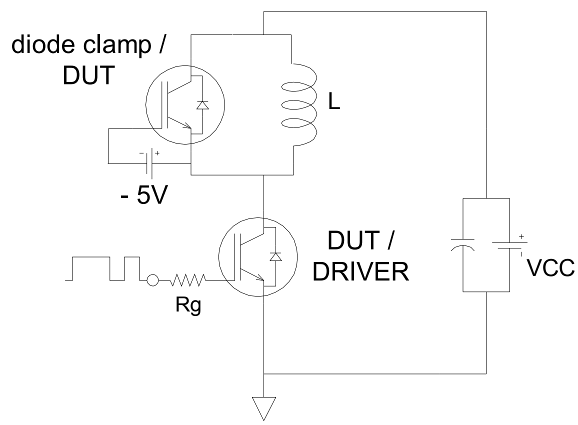


Fig.C.T.4 - Switching Loss Circuit

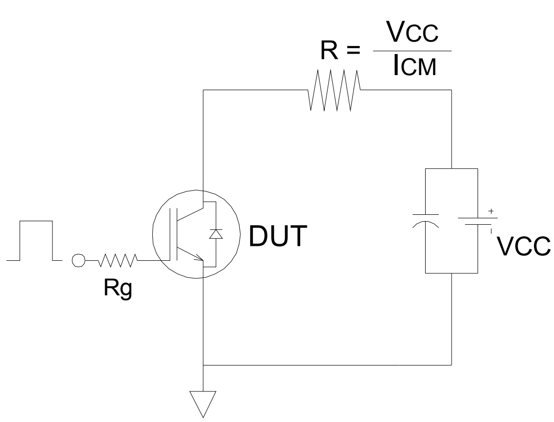


Fig.C.T.5 - Resistive Load Circuit

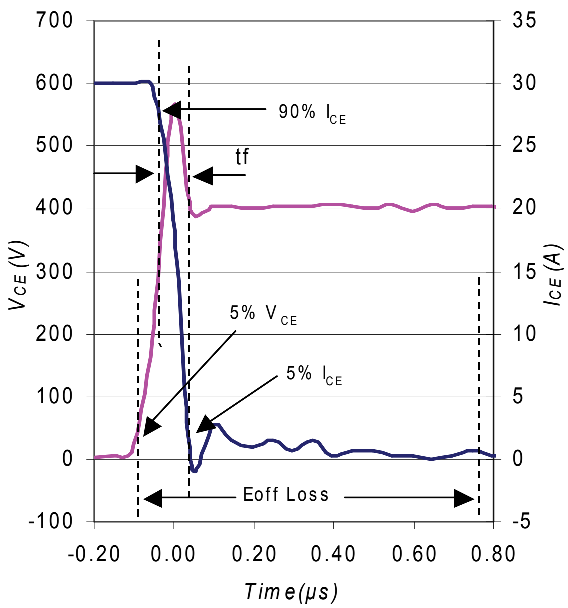


Fig. WF1 - Typ. Turn-off Loss Waveform
@ T_J = 150°C using Fig. CT.4

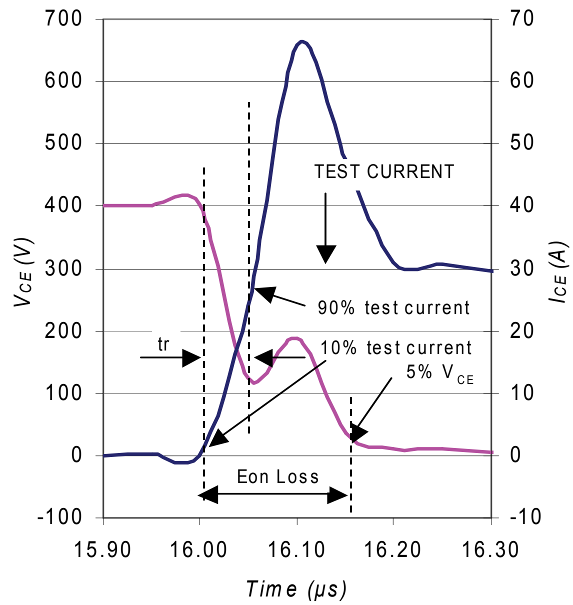


Fig. WF2 - Typ. Turn-on Loss Waveform
@ T_J = 150°C using Fig. CT.4

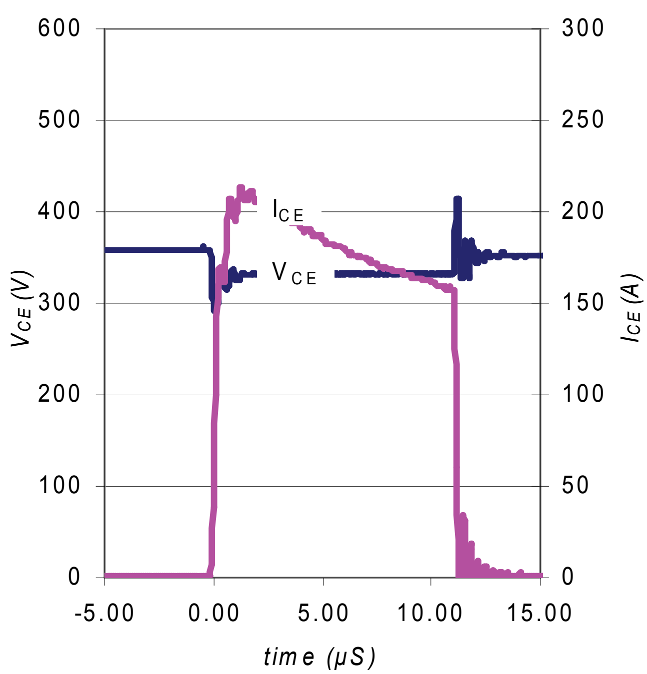
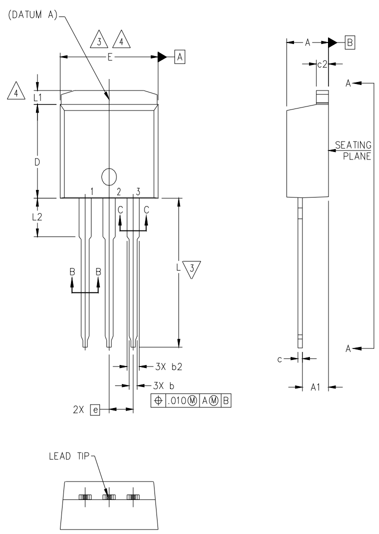


Fig. WF3 - Typ. S.C. Waveform
@ T_J = 150°C using Fig. CT.3

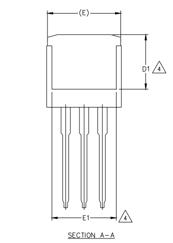
TO-262 Package Outline

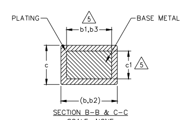
(Dimensions are shown in millimeters (inches))



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
5. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
6. CONTROLLING DIMENSION: INCH.
7.- OUTLINE CONFORM TO JEDEC TO-262 EXCEPT A1(max.), b(min.) AND D1(min.) WHERE DIMENSIONS DERIVED THE ACTUAL PACKAGE OUTLINE.





SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	2.03	3.02	.080	.119	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	5
c2	1.14	1.65	.045	.065	
D	8.38	9.65	.330	.380	3
D1	6.86	–	.270	–	4
E	9.65	10.67	.380	.420	3,4
E1	6.22	–	.245		4
e	2.54 BSC		.100 BSC		
L	13.46	14.10	.530	.555	
L1	–	1.65	–	.065	4
L2	3.56	3.71	.140	.146	

LEAD ASSIGNMENTS

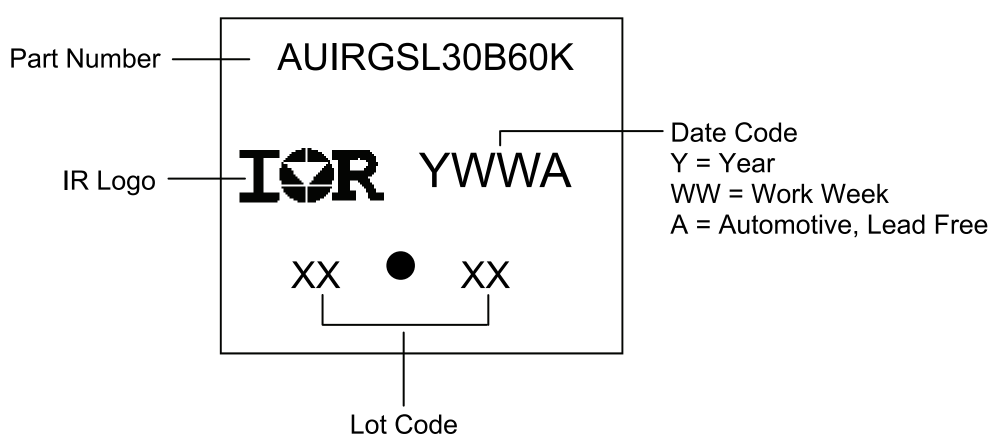
HEXFET

1.- GATE
2.- DRAIN
3.- SOURCE
4.- DRAIN

IGBTs, CoPACK

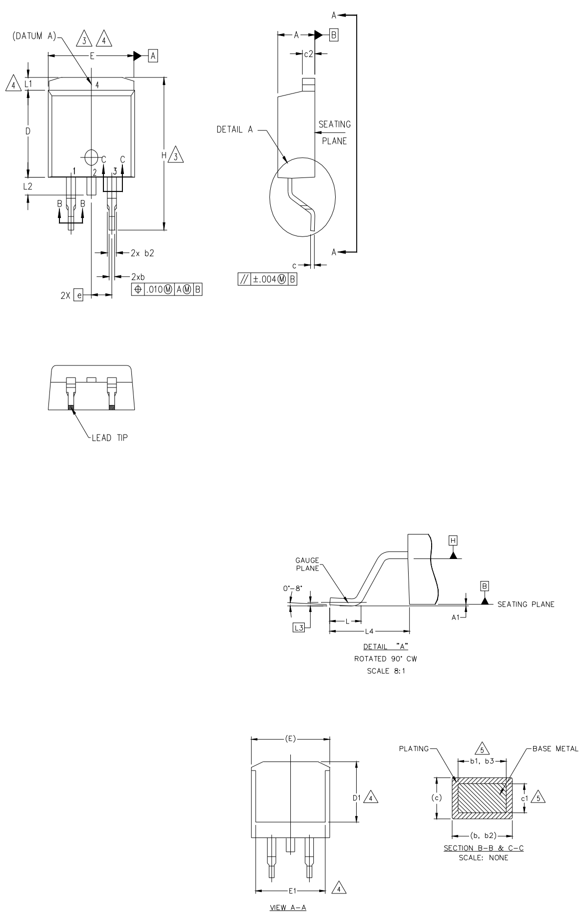
1.- GATE
2.- COLLECTOR
3.- EMITTER
4.- COLLECTOR

TO-262 Part Marking Information



D2 Pak (TO-263AB) Package Outline

(Dimensions are shown in millimeters (inches))



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
5. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
6. DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
7. CONTROLLING DIMENSION: INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-263AB.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	0.00	0.254	.000	.010	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	5
c2	1.14	1.65	.045	.065	
D	8.38	9.65	.330	.380	3
D1	6.86	-	.270		4
E	9.65	10.67	.380	.420	3,4
E1	6.22	-	.245		4
e	2.54 BSC		.100 BSC		
H	14.61	15.88	.575	.625	
L	1.78	2.79	.070	.110	
L1	-	1.65	-	.066	4
L2	1.27	1.78	-	.070	
L3	0.25 BSC		.010 BSC		
L4	4.78	5.28	.188	.208	

LEAD ASSIGNMENTS

HEXFET

1.- GATE
2, 4.- DRAIN
3.- SOURCE

IGBTs, CoPACK

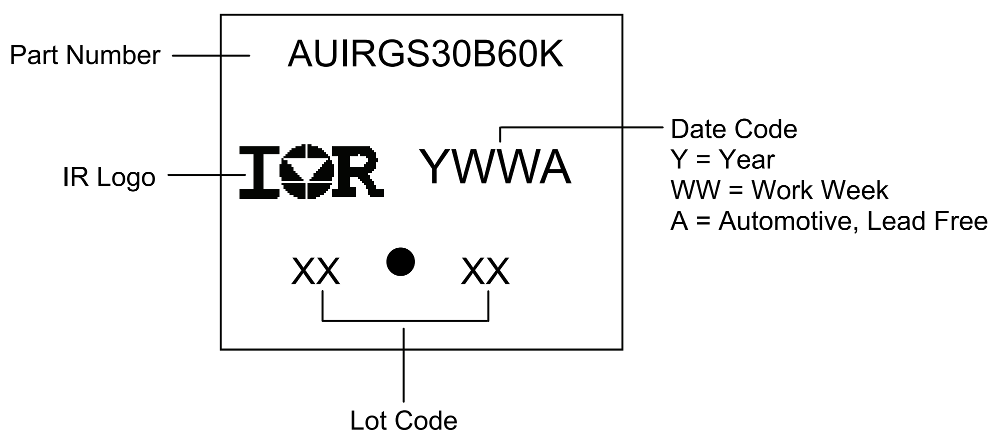
1.- GATE
2, 4.- COLLECTOR
3.- EMITTER

DIODES

1.- ANODE *
2, 4.- CATHODE
3.- ANODE

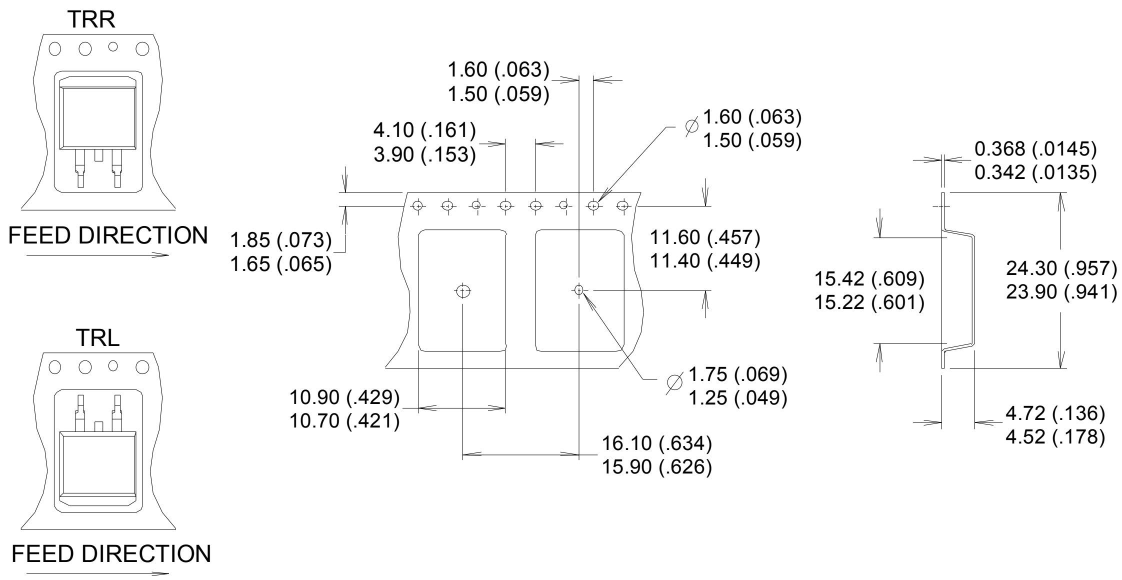
* PART DEPENDENT.

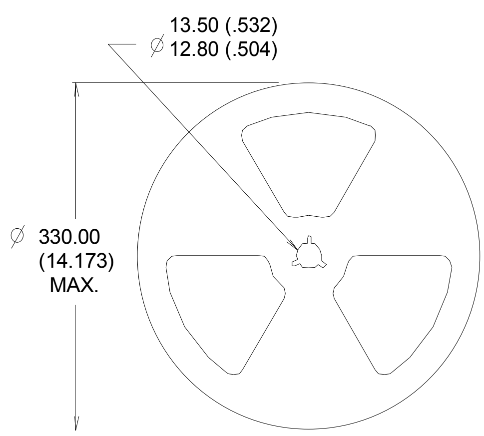
D2 Pak (TO-263AB) Part Marking Information

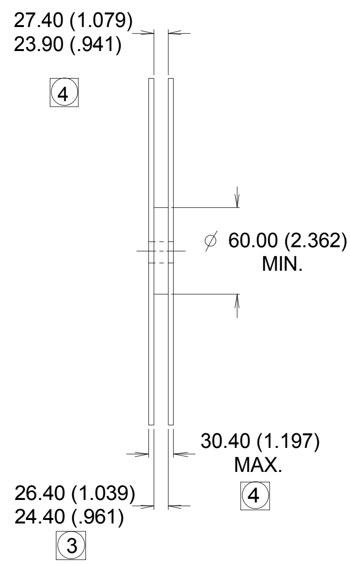


D2Pak Tape & Reel Information

(Dimensions are shown in millimeters (inches))







NOTES :

1. COMFORMS TO EIA-418.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION MEASURED @ HUB.
4. INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Qualification Information

Qualification Level		Automotive (per AEC-Q101)	
		This part number(s) passed Automotive qualification. Infineon's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		TO-262	N/A
		D2 PAK	MSL1
ESD	Machine Model	Class M4(+/- 400V)† AEC-Q101-002	
	Human Body Model	Class H2(+/- 4000V)† AEC-Q101-001	
	Charged Device Model	Class C4 (+/- 1000V)† AEC-Q101-005	
RoHS Compliant		Yes	

† Highest passing voltage.

Revision History

Date	Comments
09/08/2017	• Updated datasheet with corporate template • Corrected part marking on pages 10,11.

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